

Substitute for Form 1449(A)(PTO)

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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JUN 12 2003
PATENT & TRADEMARK OFFICE

Complete if Known	
Application Number	09/45535
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David
TECHNOLOGY CENTER 2422	JUN 13 2003
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Attorney Docket No: 1303.026US1

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Supplementary Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 606. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. If applicant's unique citation designation number (optional) is present, place a check mark here if English language Translation is attached.

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Application Number	09/45535	TECHNOLOGY CENTER 2800
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Examiner Name	Blum, David	

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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